

PG-TO220-3

MOSFET

OptiMOS™ 6 Power-Transistor, 150 V

Features

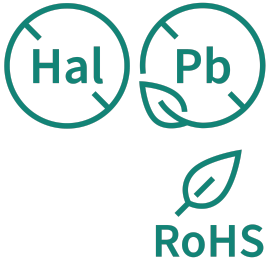
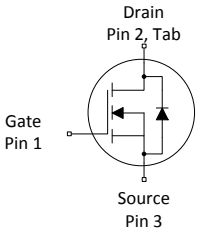
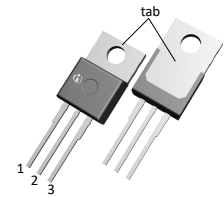
- N-channel, normal level
- Very low on-resistance $R_{DS(on)}$
- Superior thermal resistance
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	8.9	mΩ
I_D	88	A
Q_{oss}	89	nC
Q_G	29	nC
Q_{rr} (500A/μs)	111	nC



Type/Ordering Code	Package	Marking	Related Links
IPP089N15NM6	PG-TO220-3	089N15N6	-



Table of Contents

Description 1

Maximum ratings 3

Thermal characteristics 3

Electrical characteristics 4

Electrical characteristics diagrams 6

Package Outlines 10

Revision History 11

Trademarks 11

Disclaimer 11

1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	88 62 58 13.6	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=8\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=40\text{ °C/W}$ ²⁾
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	352	A	$T_C=25\text{ °C}$
Avalanche current, single pulse ⁴⁾	I_{AS}	-	-	32	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	427	mJ	$I_D=10\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	158 3.8	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=40\text{ °C/W}$ ²⁾
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.95	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁵⁾	R_{thJA}	-	-	40	°C/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	°C/W	-

⁵⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	3.0	3.5	4.0	V	$V_{DS}=V_{GS}$, $I_D=73\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance ⁶⁾	$R_{DS(on)}$	-	7.1 7.7 8.7	8.4 8.9 10.3	m Ω	$V_{GS}=15\text{ V}$, $I_D=32\text{ A}$ $V_{GS}=10\text{ V}$, $I_D=32\text{ A}$ $V_{GS}=8\text{ V}$, $I_D=16\text{ A}$
Gate resistance	R_G	-	0.74	1.11	Ω	-
Transconductance	g_{fs}	27	54	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=32\text{ A}$

⁶⁾ $R_{DS(on)}$ is specified at a distance of 1.8 mm distance to the package body; mounting at a larger distance increases the overall package resistance of approximately 0.04 mOhm/mm per leg.

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance ⁷⁾	C_{iss}	-	2100	2700	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Output capacitance ⁷⁾	C_{oss}	-	660	860	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ⁷⁾	C_{rss}	-	12	18	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	13	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=16\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	12	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=16\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	16	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=16\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	8	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=16\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

⁷⁾ Defined by design. Not subject to production test.

Table 6 Gate charge characteristics ⁸⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate to source charge ⁹⁾	Q_{gs}	-	11.1	14.4	nC	$V_{DD}=75\text{ V}$, $I_D=16\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	7.2	-	nC	$V_{DD}=75\text{ V}$, $I_D=16\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ⁹⁾	Q_{gd}	-	7	10.5	nC	$V_{DD}=75\text{ V}$, $I_D=16\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	10.9	-	nC	$V_{DD}=75\text{ V}$, $I_D=16\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ⁹⁾	Q_g	-	29	38	nC	$V_{DD}=75\text{ V}$, $I_D=16\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=75\text{ V}$, $I_D=16\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	24	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ⁹⁾	Q_{oss}	-	89	116	nC	$V_{DS}=75\text{ V}$, $V_{GS}=0\text{ V}$

⁸⁾ See "Gate charge waveforms" for parameter definition

⁹⁾ Defined by design. Not subject to production test.

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	88	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	352	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.86	1.0	V	$V_{GS}=0\text{ V}$, $I_F=32\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time ¹⁰⁾	t_{rr}	-	36	72	ns	$V_R=75\text{ V}$, $I_F=16\text{ A}$, $di_F/dt=500\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁰⁾	Q_{rr}	-	111	222	nC	$V_R=75\text{ V}$, $I_F=16\text{ A}$, $di_F/dt=500\text{ A}/\mu\text{s}$
Reverse recovery time ¹⁰⁾	t_{rr}	-	36	72	ns	$V_R=75\text{ V}$, $I_F=16\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁰⁾	Q_{rr}	-	207	414	nC	$V_R=75\text{ V}$, $I_F=16\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$

¹⁰⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

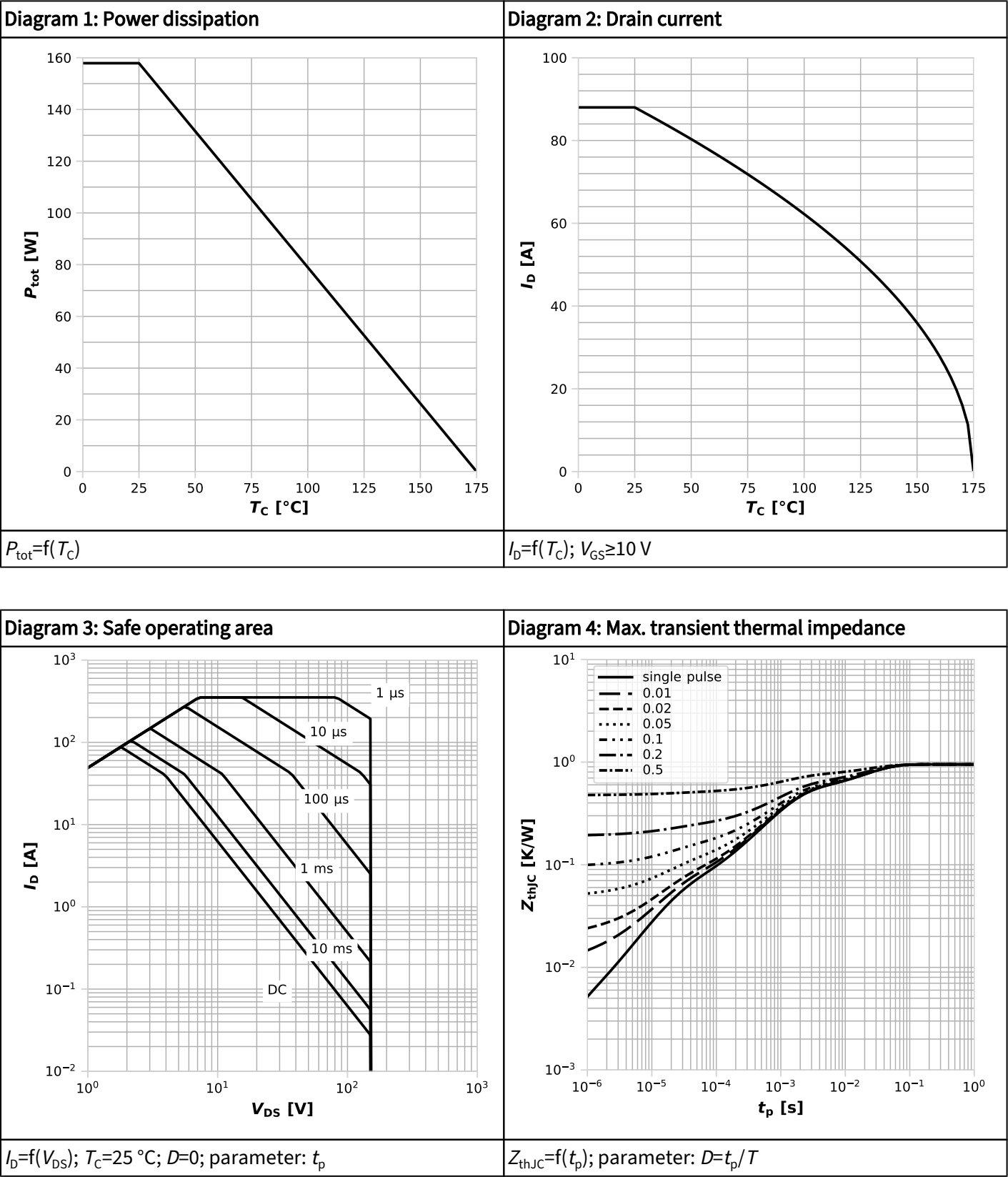
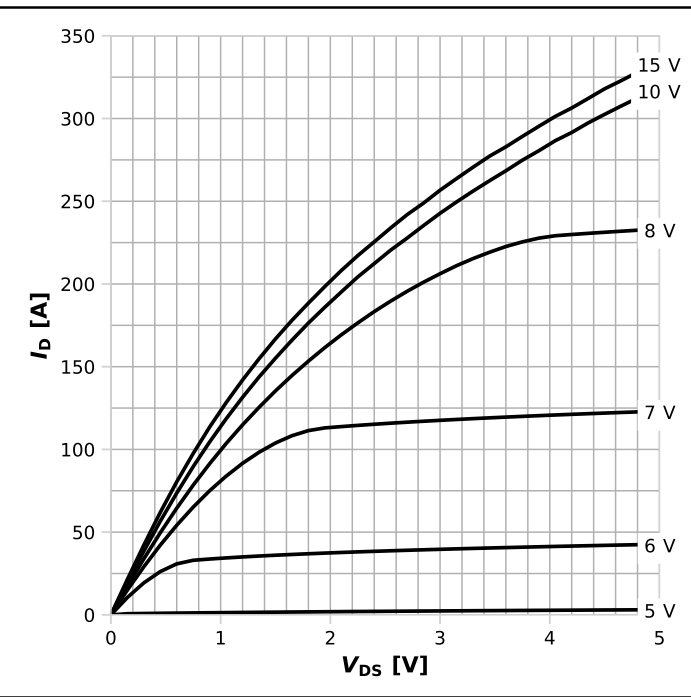
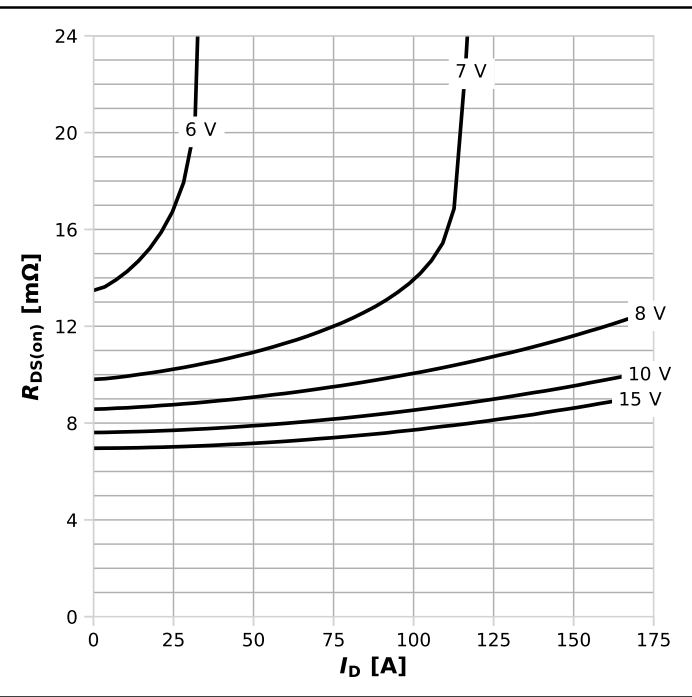


Diagram 5: Typ. output characteristics



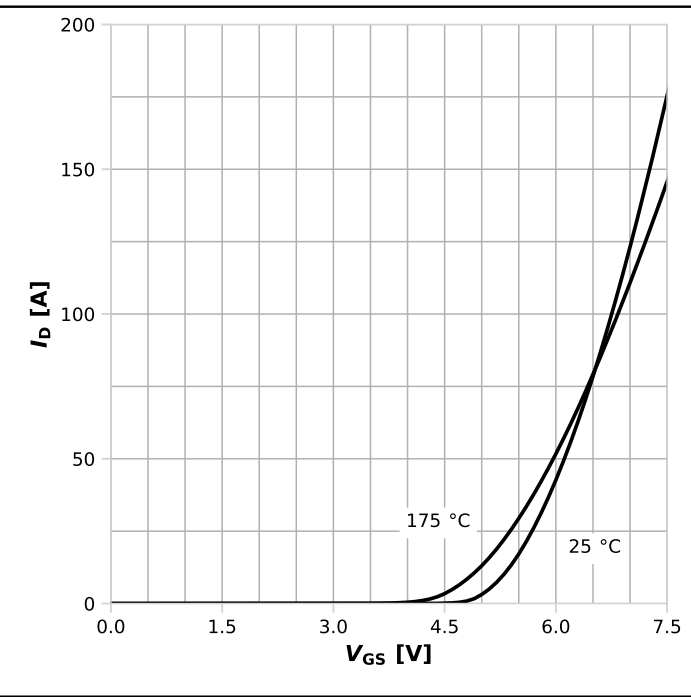
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



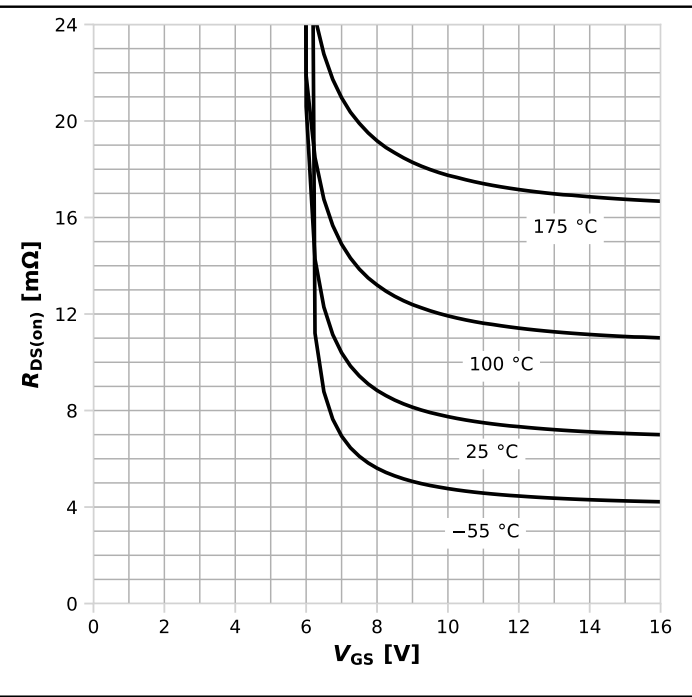
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



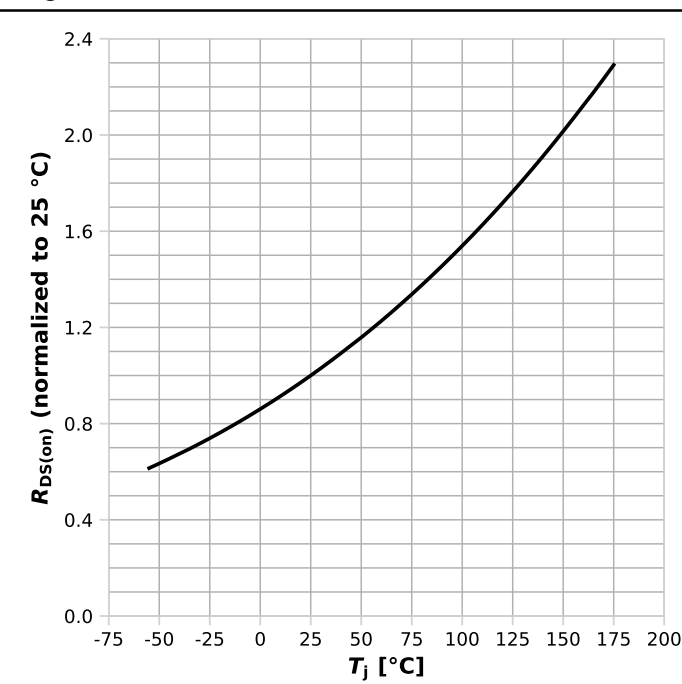
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)\max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



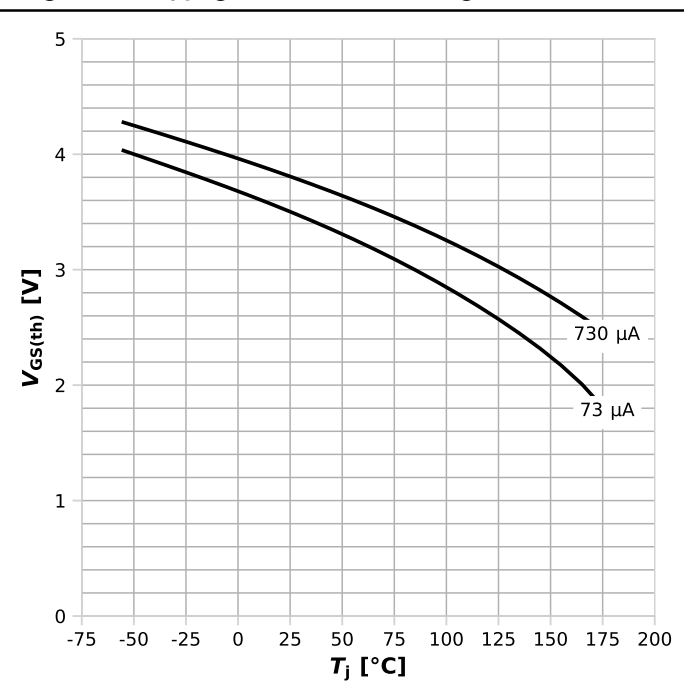
$R_{DS(on)} = f(V_{GS})$, $I_D = 32\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



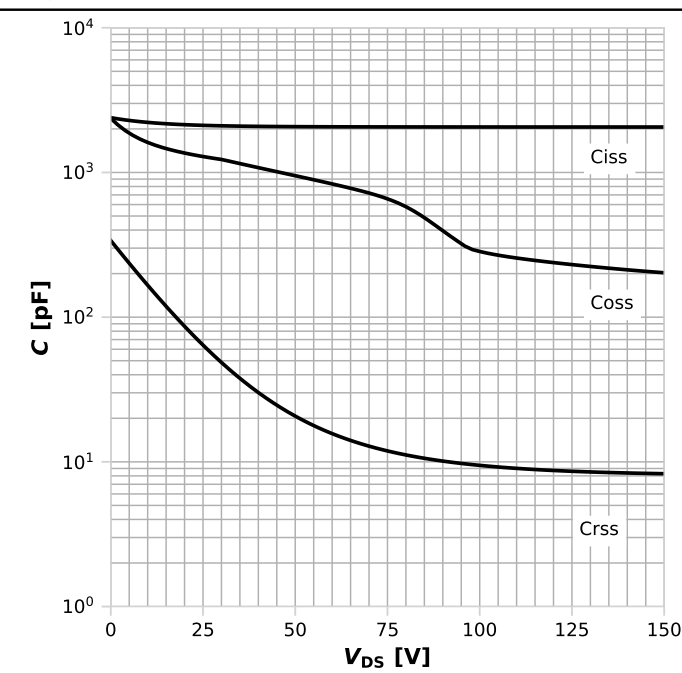
$R_{DS(on)} = f(T_j)$, $I_D = 32$ A, $V_{GS} = 10$ V

Diagram 10: Typ. gate threshold voltage



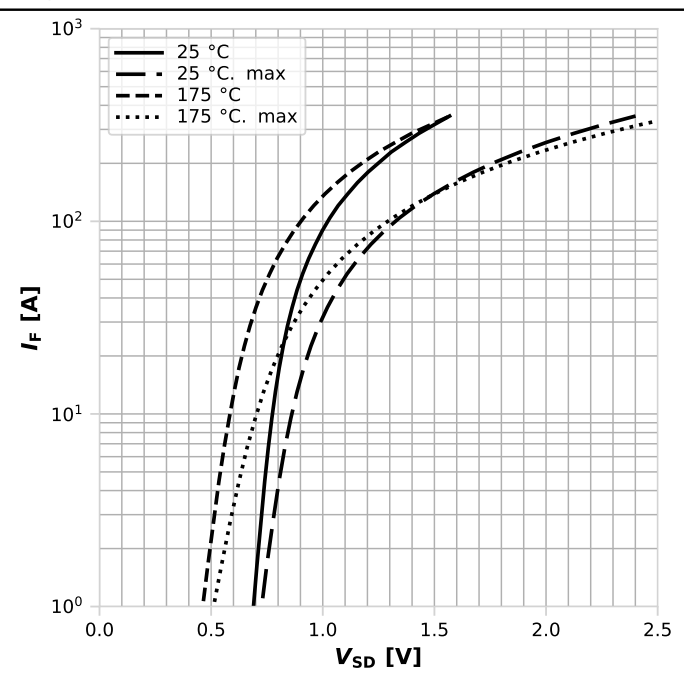
$V_{GS(th)} = f(T_j)$, $V_{GS} = V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



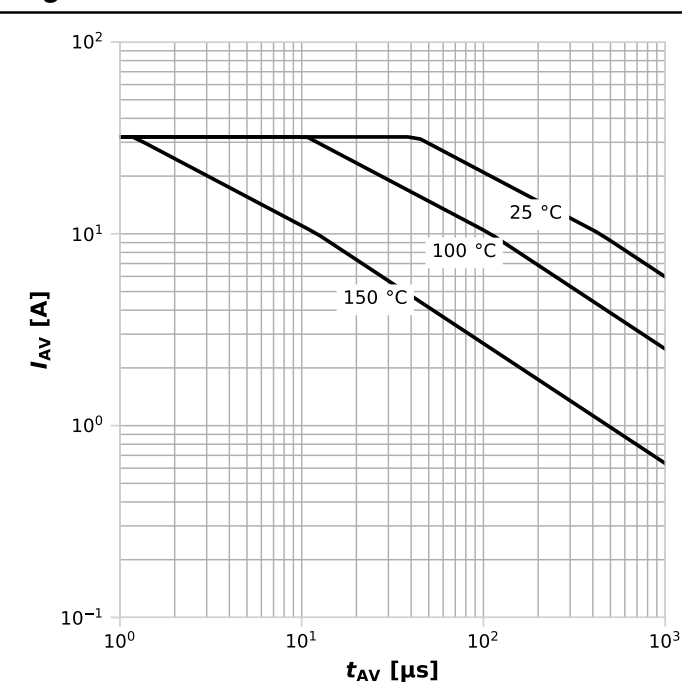
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz

Diagram 12: Forward characteristics of reverse diode



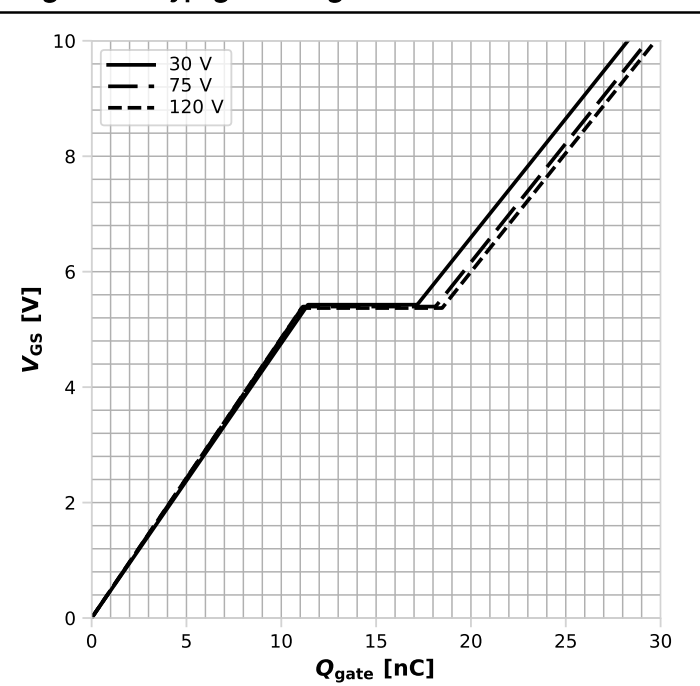
$I_F = f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



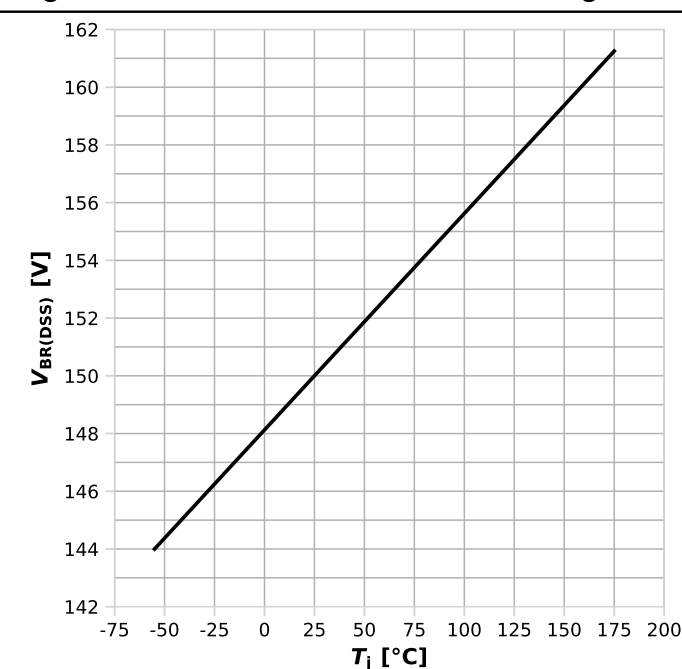
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



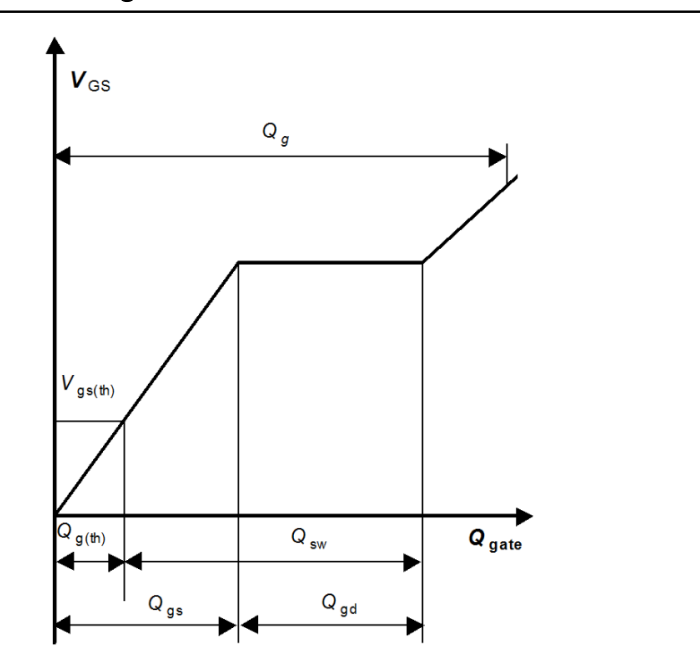
$V_{GS}=f(Q_{gate})$, $I_D=16\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Min. drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$; $I_D=1\text{ mA}$

Gate charge waveforms



-

5 Package Outlines

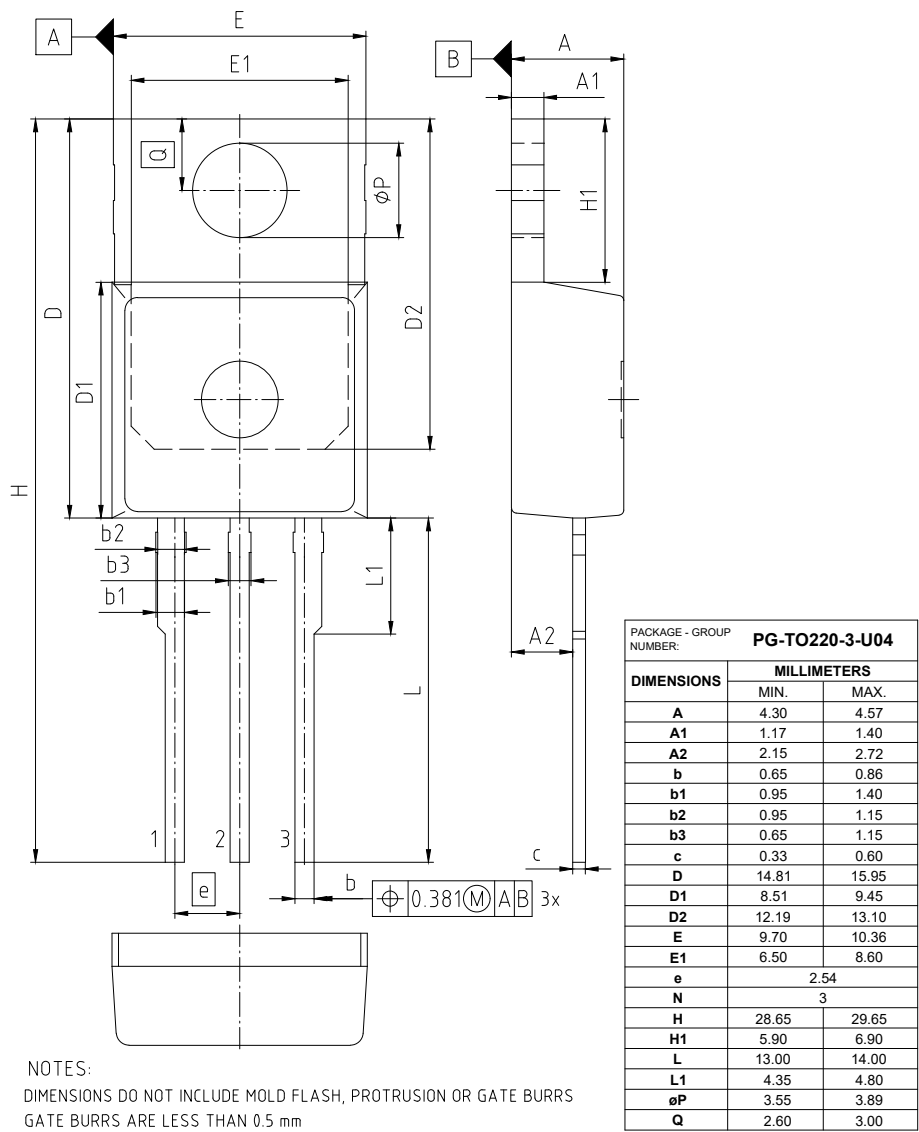


Figure 1 Outline PG-TO220-3, dimensions in mm

Revision History

IPP089N15NM6

Revision 2024-04-22, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.0	2024-03-15	Release of preliminary version
2.0	2024-04-22	Release of final

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